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July 2012

FDS6680A

Single N-Channel, Logic Level, PowerTrench® MOSFET

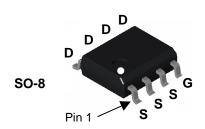
General Description

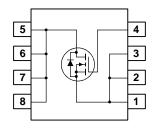
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 12.5 A, 30 V $R_{DS(ON)} = 9.5 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$ $R_{DS(ON)} = 13 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$
- Ultra-low gate charge
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- · High power and current handling capability





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
I _D	Drain Current - Continuous	(Note 1a)	12.5	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Case	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	

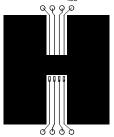
Package Marking and Ordering Information

Device Marking Device		Reel Size	Tape width	Quantity	
FDS6680A	FDS6680A	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
	acteristics		ı			l
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		25		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μА
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	μА
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Chara	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4.9		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \qquad I_D = 12.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \qquad I_D = 10.5 \text{ A}$ $V_{GS} = 10 \text{ V}, \qquad I_D = 12.5 \text{ A}, T_J = 125^{\circ}\text{C}$		7.8 9.9 11.0	9.5 13 15	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	25	11.0	13	Α
9FS	Forward Transconductance	$V_{DS} = 15 \text{ V}, \qquad V_{DS} = 3 \text{ V}$		64		S
	: Characteristics	VDS = 10 V, ID = 12.0 /		0.		
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1620		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		380		pF
C _{rss}	Reverse Transfer Capacitance			160		pF
R _G	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz		1.3		Ω
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_{D} = 1 \text{ A},$		10	19	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		5	10	ns
t _{d(off)}	Turn-Off Delay Time			27	43	ns
t _f	Turn-Off Fall Time			15	27	ns
Q _g	Total Gate Charge	$V_{DS} = 15 \text{ V}, \qquad I_{D} = 12.5 \text{ A},$		16	23	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		5		nC
Q_{gd}	Gate-Drain Charge			5.8		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A}$ (Note 2)		0.73	1.2	V
t _{rr}	Diode Reverse Recovery Time	$I_F = 12.5 \text{ A}, d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		28		ns
Q _{rr}	Diode Reverse Recovery Charge	7		18		nC

Notes:

1. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{QJC} is guaranteed by design while R_{QCA} is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s,$ Duty Cycle < 2.0%

Typical Characteristics

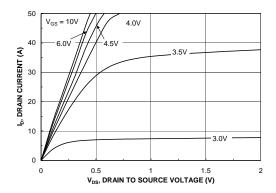


Figure 1. On-Region Characteristics.

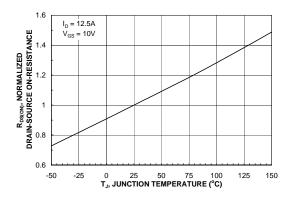


Figure 3. On-Resist ance Variation with Temperature.

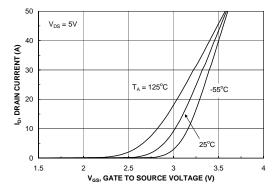


Figure 5. Transfer Characteristics.

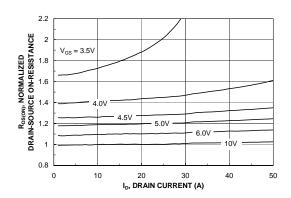


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

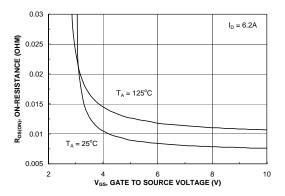


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

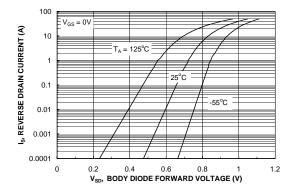
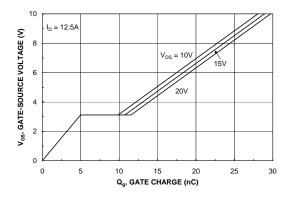


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



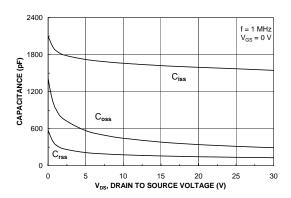
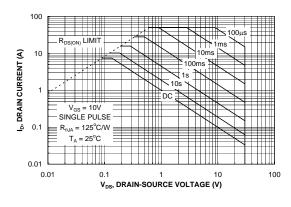


Figure 7. Gate Charge Characteristics.





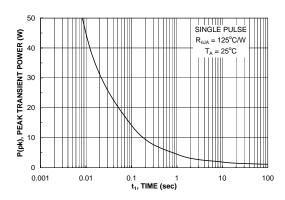


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

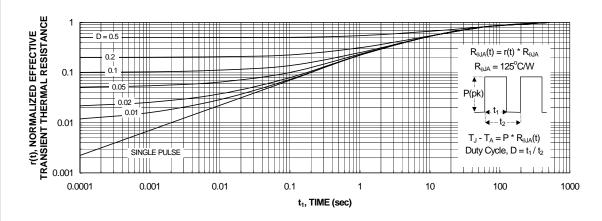


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





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